

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 250 V
- Complementary to 2STA2120
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Application

■ Audio power amplifier

Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour. solete Productle

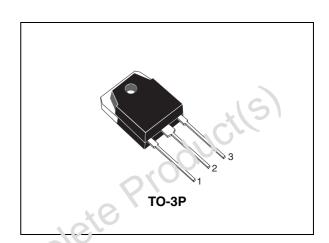


Figure 1. Internal schematic diagram

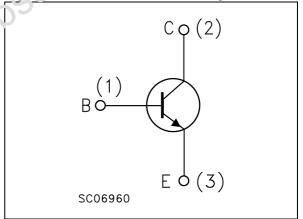


Table 1. **Device summary**

Order code	Marking	Package	Packaging
2STC5948	2STC5948	TO-3P	Tube

Electrical ratings 2STC5948

1 Electrical ratings

Table 2. Absolute maximum rating

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Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	250	V
V_{CEO}	Collector-emitter voltage (I _B = 0)	250	V
V _{EBO}	Emitter-base voltage (I _C = 0)	6	V
I _C	Collector current	17	Α
I _{CM}	Collector peak current (t _P < 5 ms)	34	Α
P_{TOT}	Total dissipation at T _c = 25 °C	200	W
T _{stg}	Storage temperature	-65 to 150	O°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter		Value	Unit
	R _{thj-case}	Thermal resistance junction-case	n.a.	0.625	°C/W
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2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
І _{СВО}	Collector cut-off current (I _E = 0)	V _{CB} = 250 V			5	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V			5	μΑ
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA	250		1/9	V
V _{(BR)CBO}	Collector-base breakdown	I _C = 100 μA	250	UC		V
V _{(BR)EBO} (1)	Emitter-base breakdown voltage ($I_C = 0$)	I _E = 1 mA	(°)	<i>y</i>		٧
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_C = 8 \text{ A}$ $I_B = 8 \text{ CO mA}$			3	V
V _{BE} ⁽¹⁾	Base-emitter voltage	$I_C = 7 \text{ A}$ $V_{CE} = 5 \text{ V}$			1.5	٧
h _{FE}	DC current gain	$I_C = 1 \land$ $V_{CE} = 5 \lor$ $V_{CE} = 5 \lor$	80 35		160	
f _T	Transition frequency	$I_C = 1 A$ $V_{CE} = 5 V$		25		MHz

^{1.} Pulsed duration = 300 μs, duty cyclε ≤ 1.5%

Electrical characteristics 2STC5948

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve

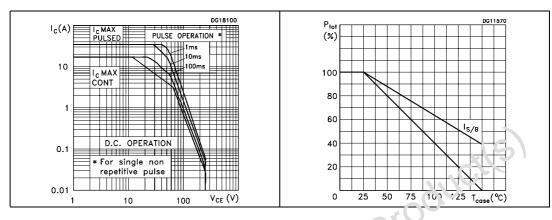


Figure 4. Output characteristics

Figure 5. Document gain

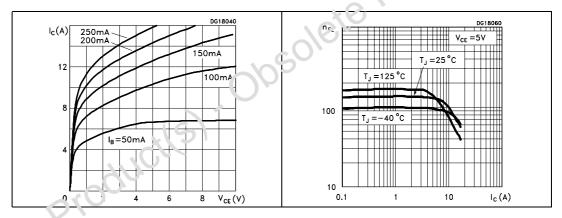
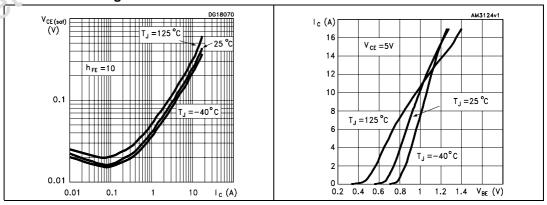


Figure 3. Collector-emitter saturation voltage

Figure 7. Base-emitter voltage



3 Package mechanical data

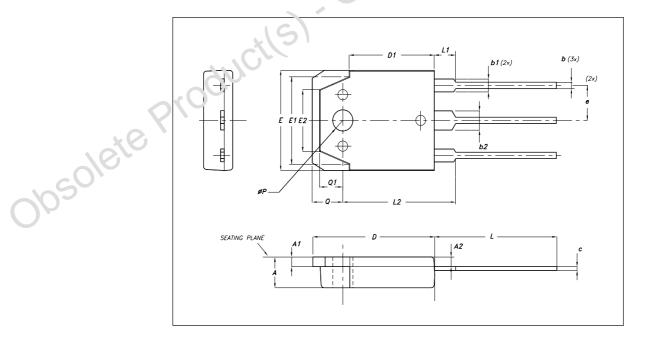
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DIM	mm.			
DIM.	MIN.	TYP	MAX.	
Α	4.6		5	
A1	1.45	1.50	1.65	
A2	1.20	1.40	1.60	
b	0.80	1	1.20	
b1	1.80		2.20	
b2	2.80		3.20	
С	0.55	0.60	0.75	
D	19.70	19.90	20.1	
D1		13.90	1110	
E	15.40		15.80	
E1		13.60	× ()	
E2		9.60	16-	
е	5.15	5.45	5.75	
L	19.50	20	20.50	
L1		3 50		
L2	18.20	1 7.40	18.60	
Р	3.10		3.30	
Q		5		
Q1		3.80		



2STC5948 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
26-Nov-2007	1	Initial release.
06-May-2008	2	New graphics
11-Jul-2008	3	Updated Figure 7.
17-Nov-2008	4	Content reworked to improve readability, no technical changes

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